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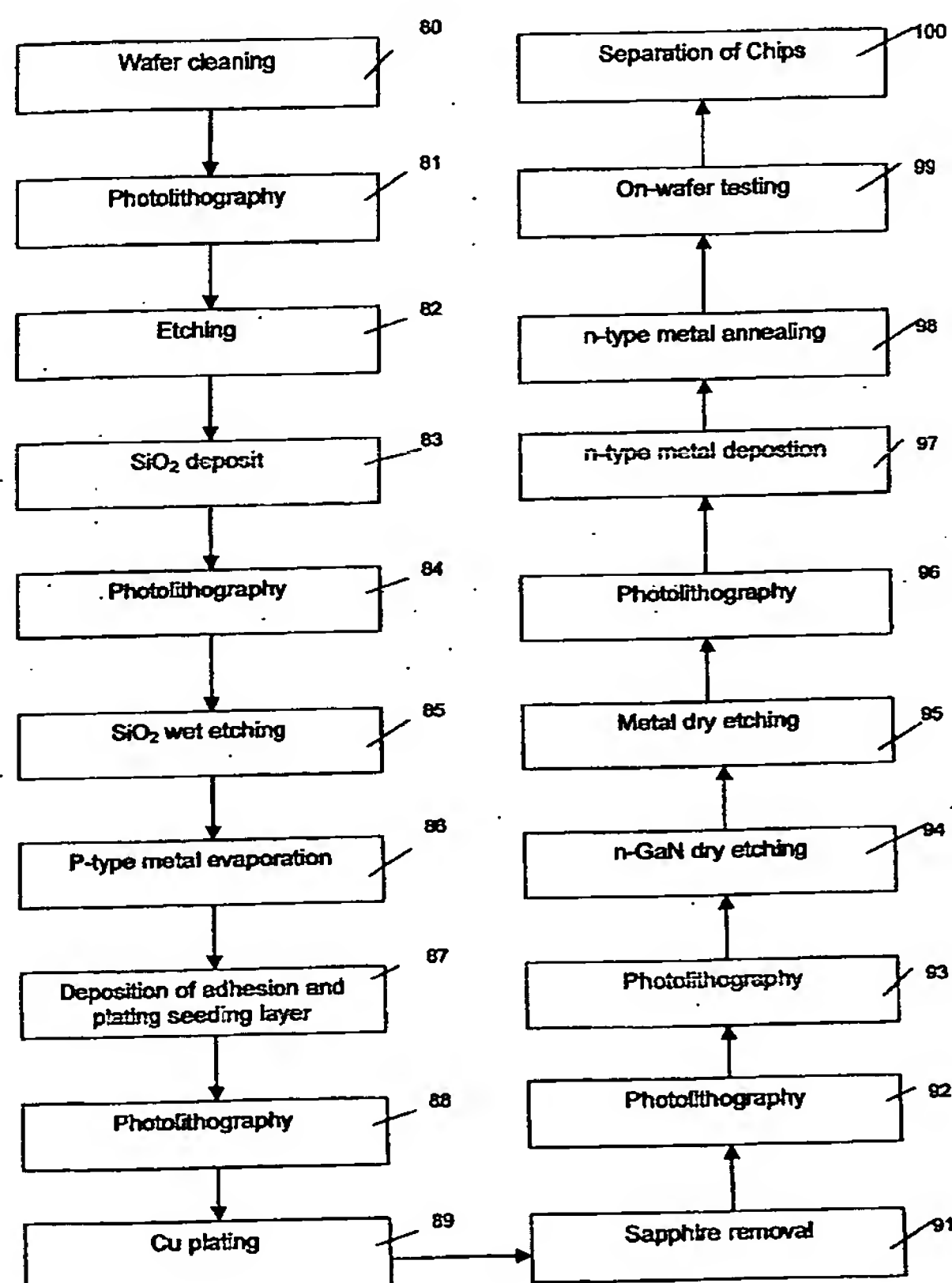
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(54) Title: FABRICATION OF SEMICONDUCTOR DEVICES



(57) Abstract: A method for fabrication of a semiconductor device on a substrate, the semiconductor having a wafer. The method includes the steps: (a) applying a seed layer of a thermally conductive metal to the wafer; (b) electroplating a relatively thick layer of the conductive metal on the seed layer; and (c) removing the substrate. A corresponding semiconductor device is also disclosed.



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